



## GaN HEMT 28V, HF-1.5GHz 180W, RF Power Transistor

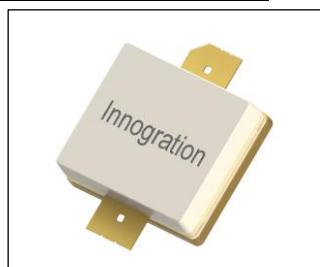
### Description

The STCH15180A2C is a 180W GaN HEMT, designed for multiple application up to 1.5GHz

It can be used in CW, Pulse and any other modulation modes. There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical class AB 960-1215MHz RF Performance with device soldered

V<sub>ds</sub>=28V, I<sub>dq</sub>=300mA, CW



Freq (MHz)	P1dB (dBm)	P1dB (W)	P1dB Eff(%)	P1dB Gain(dB)	P3dB (dBm)	P3dB (W)	P3dB Eff(%)
960	51.6	144.7	54.7	15.36	52.29	169.5	59.2
1010	51.64	146.0	57.3	15.62	52.37	172.6	60.2
1060	51.64	145.8	60.0	15.66	52.38	172.9	62.3
1110	51.67	146.8	62.8	15.43	52.5	177.9	66.2
1160	51.65	146.2	67.5	14.88	52.48	177.1	72.9
1215	51.23	132.9	69.0	14.74	52.05	160.2	73.9

### Applications

- L band power amplifier
- P band power amplifier
- ISM/RF Energy power amplifier

### Important Note: Proper Biasing Sequence for GaN HEMT Transistors

#### Turning the device ON

- Set V<sub>GS</sub> to the pinch-off (V<sub>P</sub>) voltage, typically -5 V
- Turn on V<sub>DS</sub> to nominal supply voltage
- Increase V<sub>GS</sub> until I<sub>D</sub> current is attained
- Apply RF input power to desired level

#### Turning the device OFF

- Turn RF power off
- Reduce V<sub>GS</sub> down to V<sub>P</sub>, typically -5 V
- Reduce V<sub>DS</sub> down to 0 V
- Turn off V<sub>GS</sub>

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	+200	Vdc
Gate-Source Voltage	V <sub>GS</sub>	-8 to +0.5	Vdc
Operating Voltage	V <sub>DD</sub>	50	Vdc
Maximum gate current	I <sub>GS</sub>	34	mA
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C
Case Operating Temperature	T <sub>C</sub>	+150	°C
Operating Junction Temperature	T <sub>J</sub>	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case by FEA T <sub>C</sub> = 85°C, at P <sub>diss</sub> =100W	R <sub>θJC</sub>	0.85	°C /W

**Table 3. Electrical Characteristics (TA = 25°C unless otherwise noted)**

#### DC Characteristics ( measured on wafer prior to packaging)

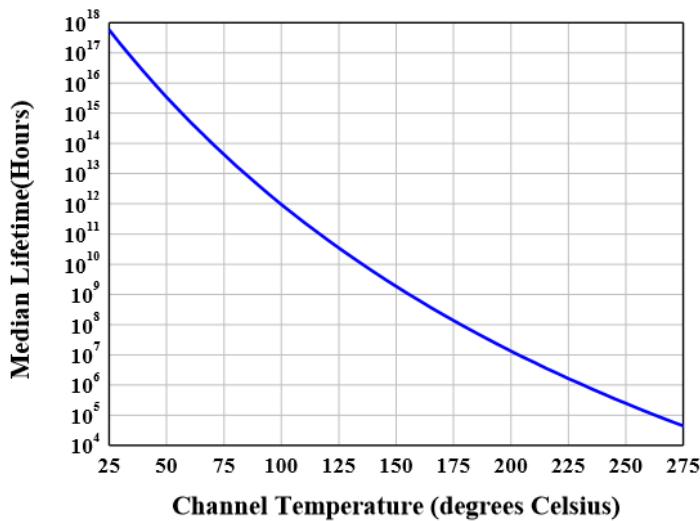
Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>GS</sub> =-8V; I <sub>D</sub> =47mA	V <sub>DSS</sub>		200		V

Gate Threshold Voltage	VDS =10V, ID = 47mA	V <sub>GS(th)</sub>	-4		-2	V
Gate Quiescent Voltage	VDS =28V, IDS=300mA, Measured in Functional Test	V <sub>GS(Q)</sub>		-3.2		V

## Ruggedness Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Load mismatch capability	1.5GHz, Pout=180W Pulsed CW All phase, No device damages	VSWR		10:1		

Figure 2: Median Lifetime vs. Channel Temperature



## 9160-1215MHz Typical performance

Figure 3: Network analyzer output S11/S21

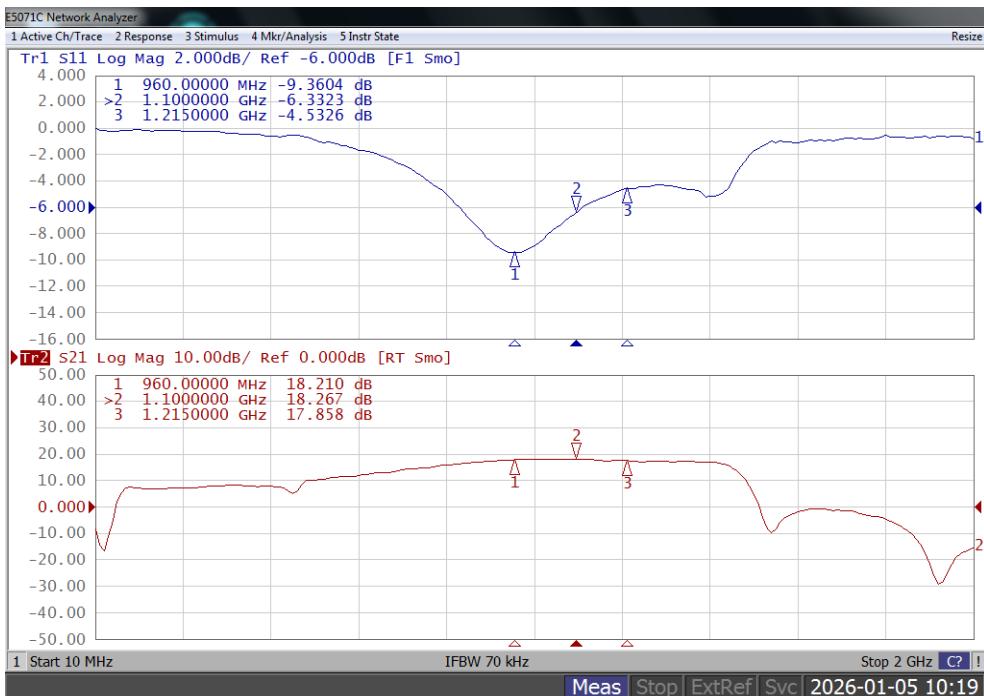
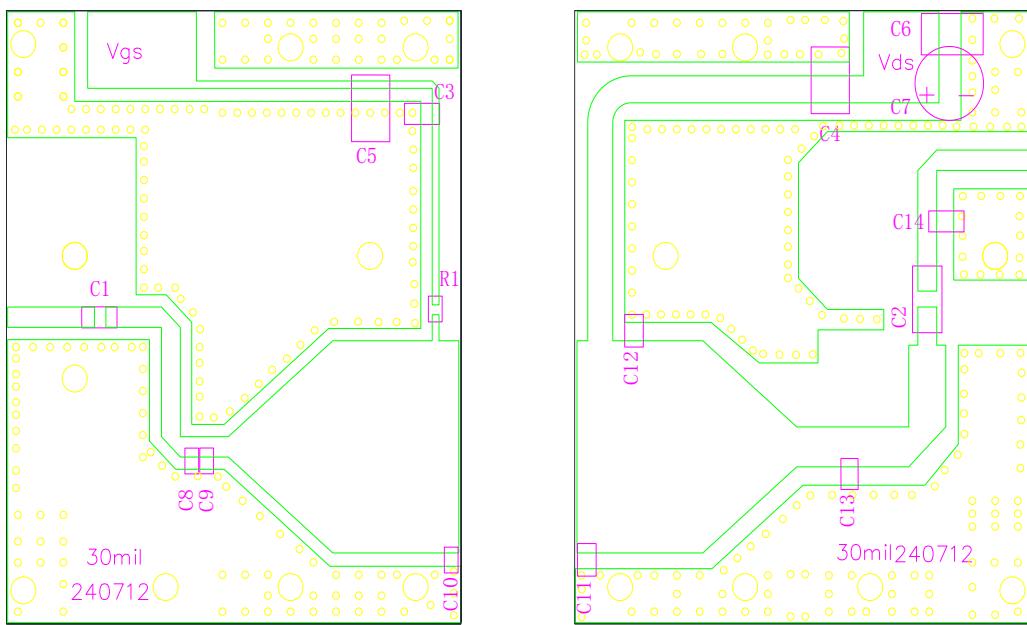


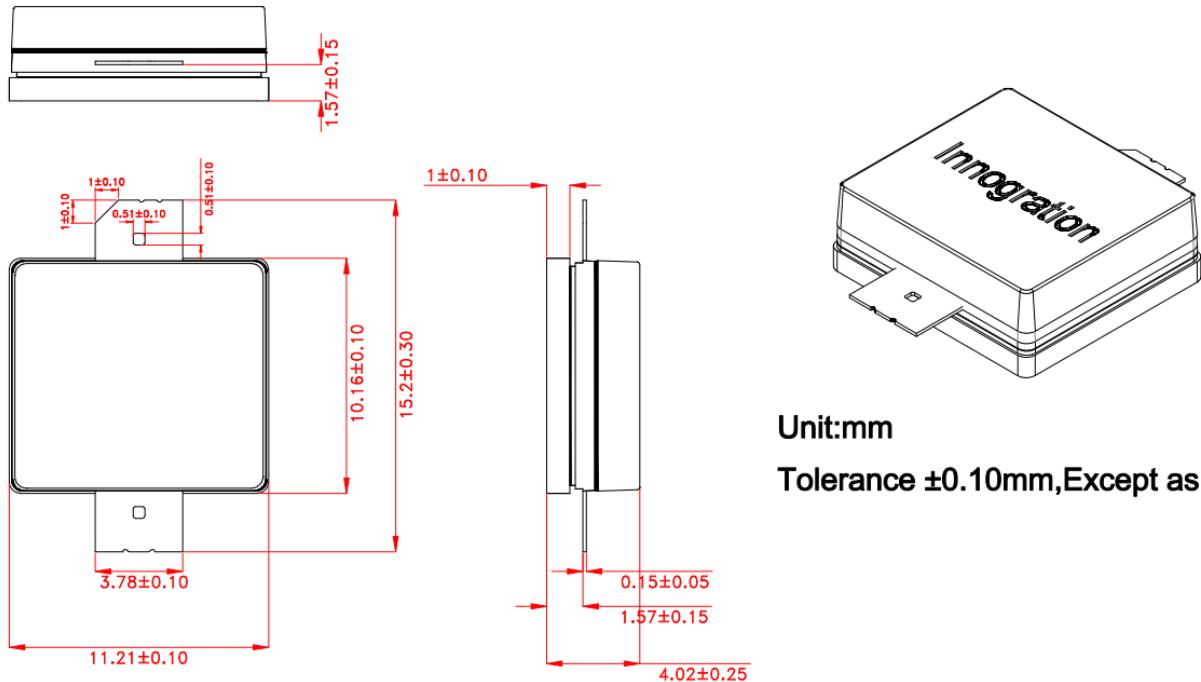
Figure 4: Picture of application board



Designator	Comment	Footprint	Quantity
C1, C10	6.8 pF	0603/0805	2
C2, C3, C4,	47 pF	0805	3
C5, C6	10uF/100V	1210	2
C7	470uF/63V		1
C8, C9, C11, C12	2.0 pF	0805	4
C13	3.0 pF	0805	1
C14	0.5 pF	0805	1
R1	10 Ω	0603	1



## Package Dimensions (Unit:mm)



Unit:mm

Tolerance ±0.10mm, Except as Noted.

## Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2026/1/5	V1.0	Preliminary Datasheet Creation

Application data based on: LSM-26-01

## Notice

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